

### General Description

The AO4852 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. As a pair these MOSFETs operate very efficiently in Push Pull and Bridge topologies.

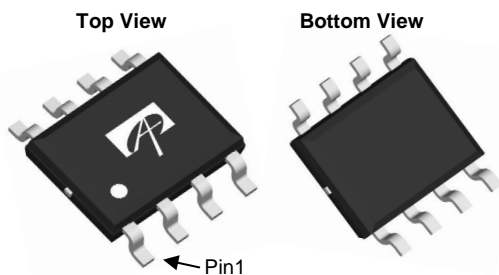
### Product Summary

$V_{DS}$  (V) = 60V  
 $I_D = 3.5A$  ( $V_{GS} = 10V$ )  
 $R_{DS(ON)} < 90m\Omega$  ( $V_{GS} = 10V$ )  
 $R_{DS(ON)} < 105m\Omega$  ( $V_{GS} = 4.5V$ )

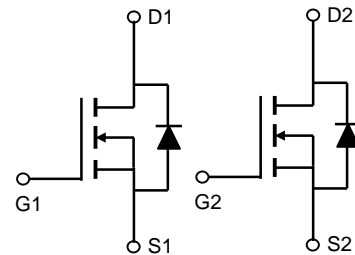
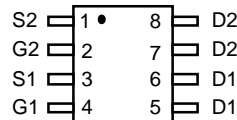
100% UIS Tested  
 100% Rg Tested



SOIC-8



Top View



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum		Units
		10 Sec	Steady State	
Drain-Source Voltage	$V_{DS}$	60		V
Gate-Source Voltage	$V_{GS}$	$\pm 20$		V
Continuous Drain Current <sup>A</sup>	$T_A=25^\circ\text{C}$	3.5	3	A
	$T_A=70^\circ\text{C}$	2.8	2.4	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	20		
Power Dissipation	$T_A=25^\circ\text{C}$	2	1.4	W
	$T_A=70^\circ\text{C}$	1.3	0.9	
Avalanche Current <sup>B</sup>	$I_{AR}$	8		A
Repetitive avalanche energy 0.3mH <sup>B</sup>	$E_{AR}$	9.6		mJ
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150		$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup> $t \leq 10s$	$R_{\theta JA}$	48	62.5	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Ambient <sup>A</sup> Steady-State		74	90	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Lead <sup>C</sup> Steady-State	$R_{\theta JL}$	33	40	$^\circ\text{C}/\text{W}$

Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
B <sub>V</sub> DSS	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			1 5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V			100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =250μA	1.7	2.3	2.6	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =10V, V <sub>DS</sub> =5V	20			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =3A T <sub>J</sub> =125°C		79 146	90 159	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A		86	105	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =3A		15		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.8	1	V
I <sub>SM</sub>	Pulsed Body-Diode Current <sup>B</sup>				20	A
I <sub>S</sub>	Maximum Body-Diode Continuous Current				2.5	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =30V, f=1MHz		372	450	pF
C <sub>oss</sub>	Output Capacitance			31		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			17		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		1.7	2.6	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub> (10V)	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, I <sub>D</sub> =3A		7.1	9.2	nC
Q <sub>g</sub> (4.5V)	Total Gate Charge			3.6		nC
Q <sub>gs</sub>	Gate Source Charge			1		nC
Q <sub>gd</sub>	Gate Drain Charge			2		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, R <sub>L</sub> =10Ω, R <sub>GEN</sub> =3Ω		4.1	5.3	ns
t <sub>r</sub>	Turn-On Rise Time			2.1		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			15		ns
t <sub>f</sub>	Turn-Off Fall Time			2.1		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =3A, di/dt=100A/μs		23.4	29	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =3A, di/dt=100A/μs		23.2		nC

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using < 300 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The SOA curve provides a single pulse rating.

Rev1: Nov. 2010

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

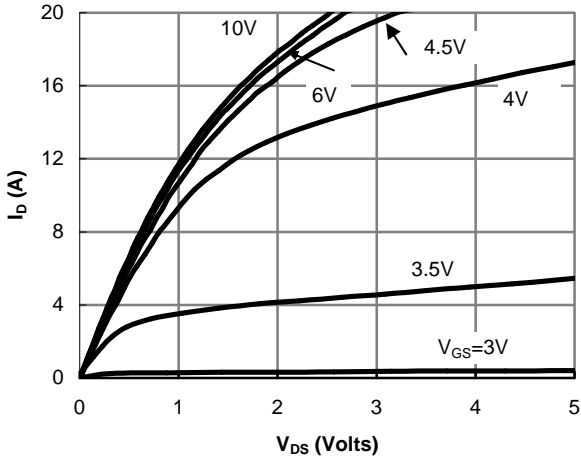


Fig 1: On-Region Characteristics

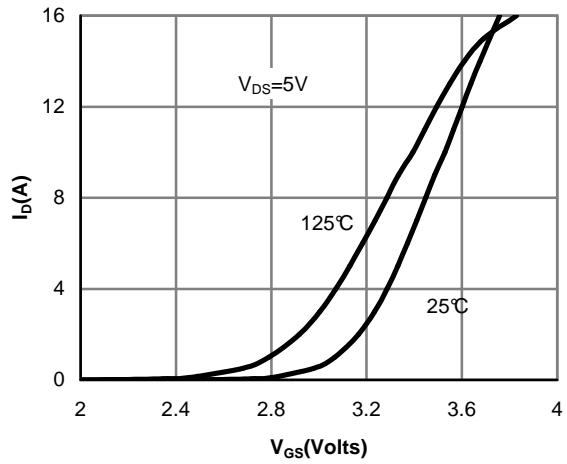


Figure 2: Transfer Characteristics

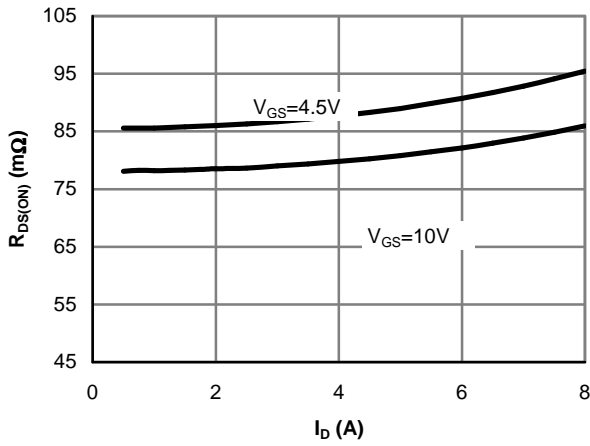


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

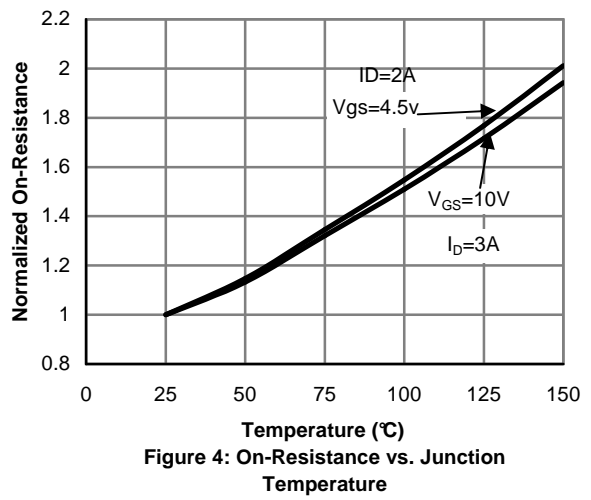


Figure 4: On-Resistance vs. Junction Temperature

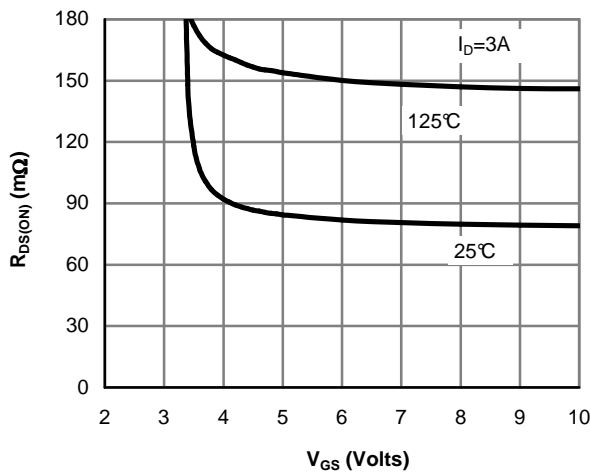


Figure 5: On-Resistance vs. Gate-Source Voltage

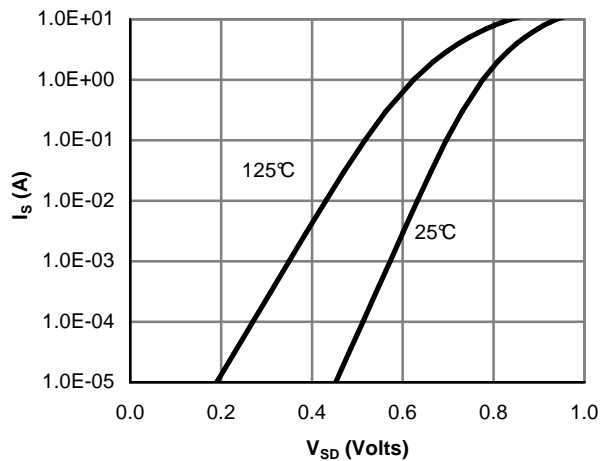


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

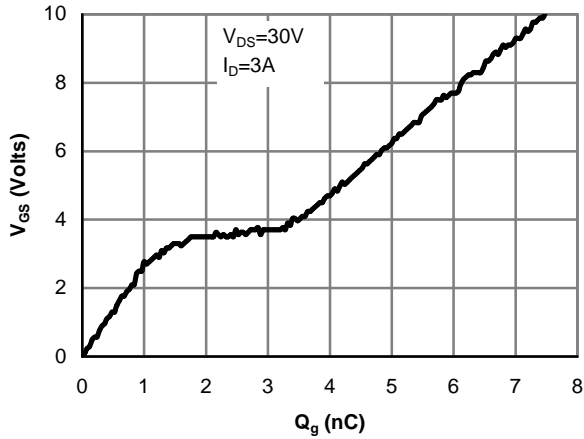


Figure 7: Gate-Charge Characteristics

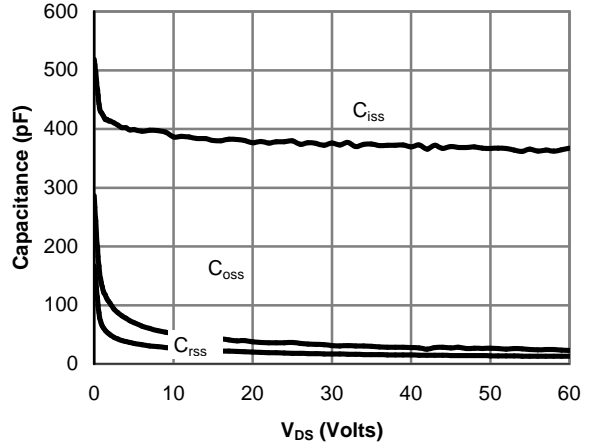


Figure 8: Capacitance Characteristics

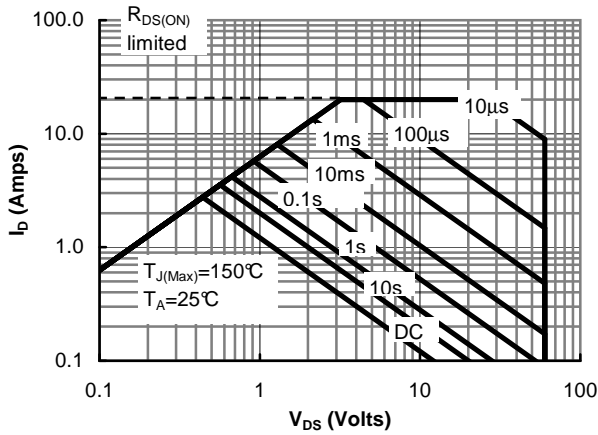


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

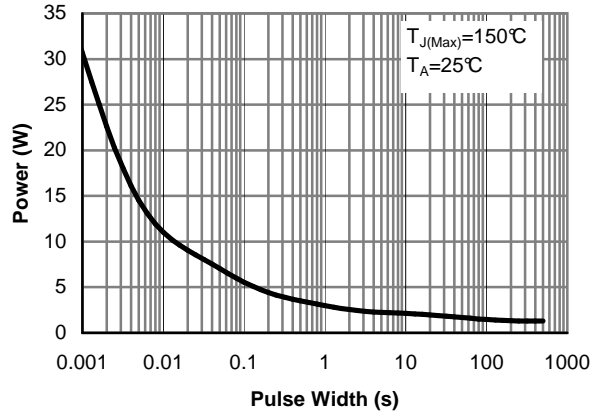


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

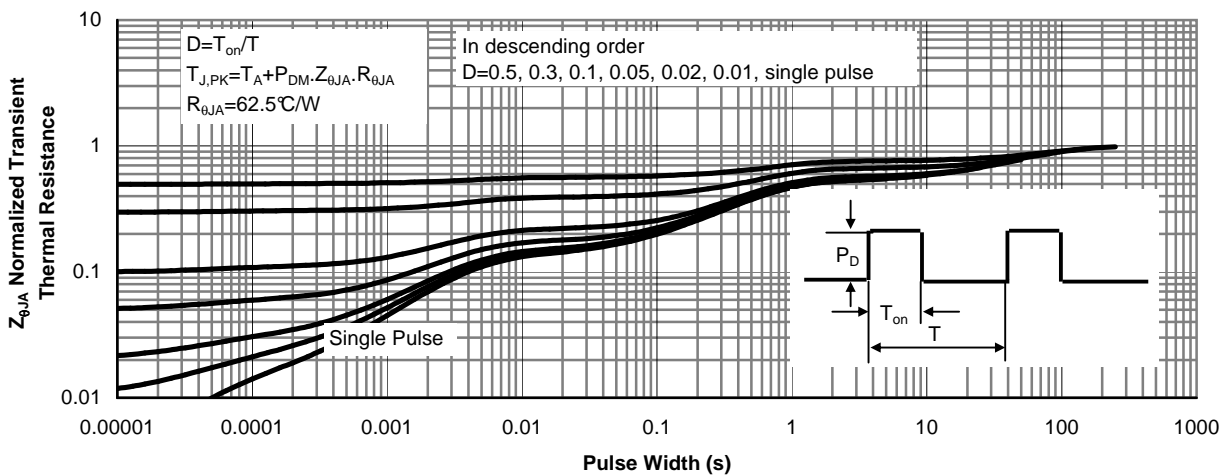


Figure 11: Normalized Maximum Transient Thermal Impedance